

Power MOSFET and Schottky Diode 30 V, 4.0 A, μ CoolF™ N-Channel, with 2.0 A Schottky Barrier Diode, 2x2 mm WDFN Package; Package: WDFN6, 2 x 2 x 0.75 mm, 0.65 mm Pitch; No of Pins: 6; Container: Tape and Reel; Qty per Container: 3000, MOSFET NFET 2X2 30V 4A 70MOHM



Images are for reference only

Manufacturers	ON Semiconductor, LLC
Package/Case	DFN-6, 2 x 2
Product Type	Transistors
RoHS	Rohs
Lifecycle	

Please submit RFQ for NTLJF4156NT1G or [Email to us: sales@ovaga.com](mailto:sales@ovaga.com) We will contact you in 12 hours.

[RFQ](#)

General Description

Power MOSFET and Schottky Diode 30 V, 4.6 A, μ CoolF™ N-Channel, with 2.0 A Schottky Barrier Diode, 2x2 mm WDFN Package

Features

WDFN Package Provides Exposed Drain Pad for Excellent Thermal Conduction

Co-Packaged MOSFET and Schottky For Easy Circuit Layout

RDS(on) Rated at Low >

Low Profile (< 0.8mm) for Easy Fit in Thin Environments

Low VF Schottky

Application

ONSEMI

Related Products



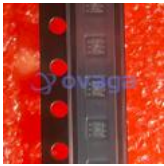
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